2.7 V to 5.5 V



2.7 V to 5.5 V Input, 3.0 A Integrated MOSFET Single Synchronous Buck DC/DC Converter

BD9B305QUZ

General Description

BD9B305QUZ is a synchronous buck DC/DC converter with built-in low on-resistance power MOSFETs. It is capable of providing current up to 3 A. It features fast transient response due to constant on-time control system. The Light Load Mode control improves efficiency in light-load conditions. It is ideal for reducing standby power consumption of equipment. Power Good function makes it possible for system to control sequence. It achieves the high power density and offer a small footprint on the PCB by employing small package.

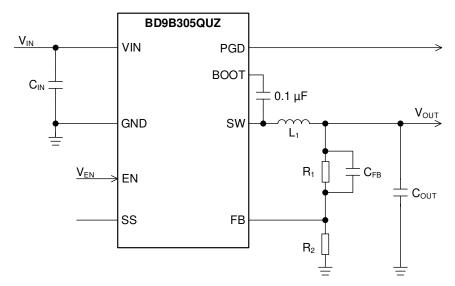
Features

- Single Synchronous Buck DC/DC Converter
- Constant On-time Control
- Light Load Mode Control
- Adjustable Soft Start
- Power Good Output
- Output Capacitor Discharge Function
- Over Voltage Protection (OVP)
- Over Current Protection (OCP)
- Short Circuit Protection (SCP)
- Thermal Shutdown Protection (TSD)
- Under Voltage Lockout Protection (UVLO)
- VMMP08LZ2020 Package Backside Heat Dissipation 0.5 mm Pitch

Applications

- Step-down Power Supply for SoC, FPGA, Microprocessor
- Laptop PC / Tablet PC / Server
- LCD TV
- Storage Device (HDD / SSD)
- Printer, OA Equipment
- Distributed Power Supply, Secondary Power Supply

Typical Application Circuit



with built-in low on-resistance power MOSFETs. It is capable of providing current up to 3 A. It features fast transient response due to constant on-time control Output Voltage Range: Output Voltage Range: Output Current: 3.0 A (Max) Switching Frequency: 1 MHz (Typ)

Key Specifications

Input Voltage Range:

Switching Frequency:
 High-Side FET ON Resistance:
 Low-Side FET ON Resistance:
 Shutdown Current:
 1 MHz (Typ)
 50 mΩ (Typ)
 40 mΩ (Typ)
 0 μA (Typ)

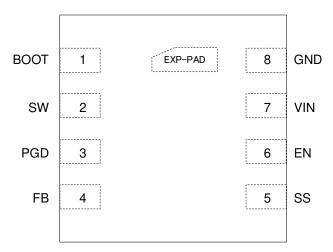
Package W (Typ) x D (Typ) x H (Max) VMMP08LZ2020 2.00 mm x 2.00 mm x 0.40 mm



VMMP08LZ2020

Pin Configuration

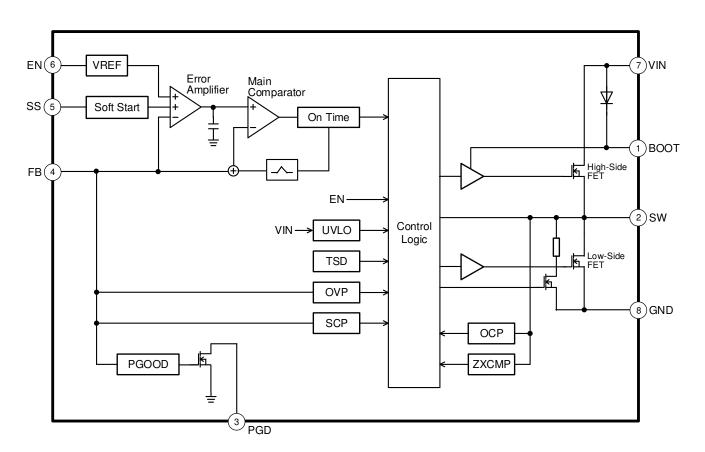
(TOP VIEW)



Pin Descriptions

Pin No.	Pin Name	Function
1	воот	Pin for bootstrap. Connect a bootstrap capacitor of 0.1 μF between this pin and the SW pin. The voltage of this pin is the gate drive voltage of the High-Side FET.
2	SW	Switch pin. This pin is connected to the source of the High-Side FET and the drain of the Low-Side FET. Connect a bootstrap capacitor of 0.1 µF between this pin and the BOOT pin. In addition, connect an inductor considering the direct current superimposition characteristic.
3	PGD	Power Good pin. This pin is an open drain output that requires a pull-up resistor. See page-17 for setting the resistance. If not used, this pin can be left floating or connected to the ground.
4	FB	Output voltage feedback pin. See page 31 for how to calculate the resistances of the output voltage setting.
5	SS	Pin for setting the soft start time of output voltage. The soft start time is 1 ms (Typ) when the SS pin is left floating. A ceramic capacitor connected to the SS pin makes the soft start time more than 1 ms. See page 31 for how to calculate the capacitance.
6	EN	Enable pin. The device starts up with setting V_{EN} to 0.920 V (Typ) or more. The device enters the shutdown mode with setting V_{EN} to 0.875 V (Typ) or less. This pin must be terminated.
7	VIN	Power supply pin. Connecting 0.1 μF (Typ) and 22 μF (Typ) ceramic capacitors is recommended. The detail of a selection is described in page 31.
8	GND	Ground pin.
-	EXP-PAD	A backside heat dissipation exposed pad. Connecting to the PCB power ground plane by using thermal vias provides excellent heat dissipation characteristics. See page 34 to 35 for the detailed PCB layout design.

Block Diagram



Description of Blocks

1. VREF

The VREF block generates the internal reference voltage.

2. Soft Start

The Soft Start circuit slows down the rise of output voltage during start-up and controls the current, which allows the prevention of output voltage overshoot and inrush current. The internal soft start time is 1 ms (Typ) when the SS pin is left floating. A capacitor connected to the SS pin makes the rising time more than 1 ms.

3. Error Amplifier

The Error Amplifier adjusts the Main Comparator input voltage to make the internal reference voltage equal to FB voltage.

4. Main Comparator

The Main Comparator compares the Error Amplifier output voltage and FB voltage (V_{FB}). When V_{FB} becomes lower than the Error Amplifier output voltage, the output turns high and reports to the On Time block that the output voltage has dropped below the control voltage.

On Time

This block generates On Time. The designed On Time is generated after the Main Comparator output turns high. The On Time is adjusted to control the frequency to be fixed even with I/O voltage is changed.

PGOOD

The PGOOD block is for power good function. When the output voltage reaches within ± 10 % (Typ) of the setting voltage, the built-in open drain Nch MOSFET connected to the PGD pin is turned off and the PGD pin becomes Hi-Z (High impedance). When the output voltage reaches outside ± 15 % (Typ) of the setting voltage, the open drain Nch MOSFET is turned on and PGD pin is pulled down with 100 Ω (Typ).

7. UVLO

The UVLO block is for under voltage lockout protection. The device is shut down when input voltage (V_{IN}) falls to 2.45 V (Typ) or less. The threshold voltage has the 100 mV (Typ) hysteresis.

8. TSD

The TSD block is for thermal protection. The device is shut down when the junction temperature Tj reaches to 175 °C (Typ) or more. The device is automatically restored to normal operation with a hysteresis of 25 °C (Typ) when the Tj goes down.

9. OVP

The OVP block is for output over voltage protection. When the FB voltage (V_{FB}) exceeds 115 % (Typ) or more of FB threshold voltage V_{FBTH} , the output MOSFETs are turned off. After V_{FB} falls 110 % (Typ) or less of V_{FBTH} , the output MOSFETs are returned to normal operation condition.

10. OCP

The OCP block is for over current protection. This function operates by limiting the current that flows through the High-Side FET and the Low-Side FET at each cycle of the switching frequency.

11. SCP

The SCP is for short circuit protection. When 256 times OCP are counted on the condition where the device completes the soft start and the output voltage falls below 85 % (Typ) of the setting voltage, the device is shut down for 128 ms (Typ). After 128 ms shutdown, the device restarts. (HICCUP operation)

12. ZXCMP

The ZXCMP is a comparator that monitors the inductor current. When inductor current falls below 0A (Typ) while the Low-Side FET is on, it turns the FET off.

13. Control Logic

The Control Logic controls the switching operation and protection function operation.

Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Rating	Unit
Input Voltage	V _{IN}	-0.3 to +7	V
EN Voltage	V _{EN}	-0.3 to +V _{IN}	V
FB Voltage	V _{FB}	-0.3 to +7	V
SS Voltage	Vss	-0.3 to +V _{IN}	V
PGD Voltage	V _{PGD}	-0.3 to +7	V
SW Voltage	Vsw	-0.3 to V _{IN} + 0.3	V
Voltage from GND to BOOT	V _{воот}	-0.3 to +14	V
Voltage from SW to BOOT	ΔV _{BOOT-SW}	-0.3 to +7	V
Output Current	Іоит	3.5	А
Maximum Junction Temperature	Tjmax	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

Thermal Resistance (Note 1)

Deremeter	Cumbal	Thermal Res	Lloit		
Parameter Parame	Symbol	1s (Note 3)	2s2p (Note 4)	Unit	
VMMP08LZ2020					
Junction to Ambient	θ_{JA}	208.30	90.30	°C/W	
Junction to Top Characterization Parameter (Note 2)	Ψ_{JT}	28.00	22.00	°C/W	

(Note 1) Based on JESD51-2A (Still-Air).

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

(Note 3) Using a PCB board based on JESD51-3.

(Note 4) Using a PCB board	based or	n JESD51-5, 7.				
Layer Number of Measurement Boa		Material	Board Size			
Single		FR-4	114.3 mm x 76.2 mm x	(1.57 mmt		
Тор						
Copper Pattern		Thickness				
Footprints and Trac	es	70 µm				
Layer Number of	f	Material	Board Size		Thermal Via ⁽	lote 5)
Measurement Boa	rd	Material	board Size		Pitch	Diameter
4 Layers		FR-4	114.3 mm x 76.2 mm	x 1.6 mmt	1.20 mm	⊅0.30 mm
Тор		2 Internal Laye	ers	Bottom		
Copper Pattern		Thickness	Copper Pattern	Thickness	Copper Pattern	Thickness
Footprints and Trac	ces	70 µm	74.2 mm x 74.2 mm	35 µm	74.2 mm x 74.2 mm	70 µm

(Note 5) This thermal via connects with the copper pattern of all layers.

Recommended Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit
Input Voltage	V _{IN}	2.7	-	5.5	V
Operating Temperature (Note 1)	Та	-40	-	+85	°C
Output Current (Note 1)	louт	0	-	3.0	Α
Output Voltage Setting	Vouт	0.6	-	V _{IN} x 0.8	V

⁽Note 1) Tj must be lower than 150 °C under the actual operating environment.

Electrical Characteristics (Unless otherwise specified Ta = 25 °C. V_{IN} = 5 V. V_{EN} = 5 V)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Input Supply						
Shutdown Current	Isdn	-	0	10	μA	V _{EN} = 0 V
Quiescent Current at No Load	lα	-	15	30	μA	I _{OUT} = 0 A, No switching
UVLO Detection Threshold Voltage	V _{UVLO1}	2.350	2.450	2.550	V	V _{IN} falling
UVLO Release Threshold Voltage	V_{UVLO2}	2.425	2.550	2.700	V	V _{IN} rising
JVLO Hysteresis Voltage	Vuvlohys	50	100	200	mV	
Enable						
EN Threshold Voltage High	VENH	0.875	0.920	0.965	V	V _{EN} rising
EN Threshold Voltage Low	V _{ENL}	0.830	0.875	0.920	V	V _{EN} falling
EN Hysteresis Voltage	VENHYS	27	45	63	mV	
EN Input Current	I _{EN}	-	0	10	μA	V _{EN} = 5 V
Reference Voltage, Error Amplifier,	Soft Start					
B Threshold Voltage	V _{FBTH}	0.591	0.600	0.609	V	PWM mode
B Input Current	I _{FB}	-	-	100	nA	V _{FB} = 0.6 V
Soft Start Time	tss	0.6	1.0	1.4	ms	SS pin is left floating.
Soft Start Charge Current	Iss	0.6	1.0	1.4	μΑ	
On Time						
On Time	t _{ON}	270	360	450	ns	V _{OUT} = 1.8 V, PWM mode
SW (MOSFET)						
High-Side FET ON Resistance	Ronh	-	50	100	mΩ	V _{BOOT} - V _{SW} = 5 V
ow-Side FET ON Resistance	Ronl	-	40	80	mΩ	
High-Side FET Leakage Current	ILKH	-	0	10	μΑ	No switching
_ow-Side FET Leakage Current	ILKL	-	0	10	μΑ	No switching
Power Good						
Power Good Rising Threshold Voltage	V _{PGDGR}	85	90	95	%	V _{FB} rising, V _{PGDGR} = V _{FB} / V _{FBTH} x 100
Power Good Falling Fhreshold Voltage	V _{PGDGF}	105	110	115	%	V _{FB} falling, V _{PGDGF} = V _{FB} / V _{FBTH} x 100
Power Fault Rising Fhreshold Voltage	V _{PGDFR}	110	115	120	%	V _{FB} rising, V _{PGDFR} = V _{FB} / V _{FBTH} x 100
Power Fault Falling Fhreshold Voltage	V _{PGDFF}	80	85	90	%	V _{FB} falling, V _{PGDFF} = V _{FB} / V _{FBTH} x 100
PGD Output Leakage Current	ILKPGD	-	0	5	μA	V _{PGD} = 5 V
PGD MOSFET ON Resistance	R _{PGD}	-	100	200	Ω	
PGD Output Low Level Voltage	V _{PGDL}	-	0.1	0.2	V	I _{PGD} = 1 mA

Typical Performance Curves

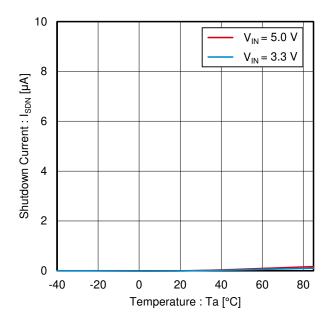


Figure 1. Shutdown Current vs Temperature

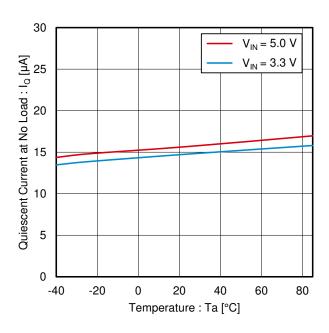


Figure 2. Quiescent Current at No Load vs Temperature

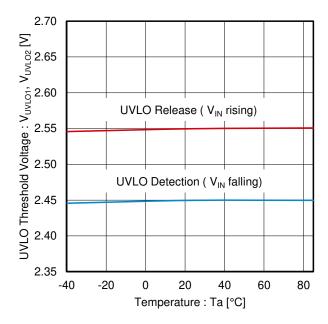


Figure 3. UVLO Threshold Voltage vs Temperature

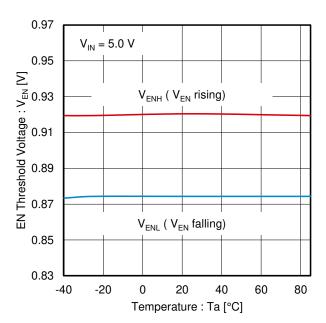
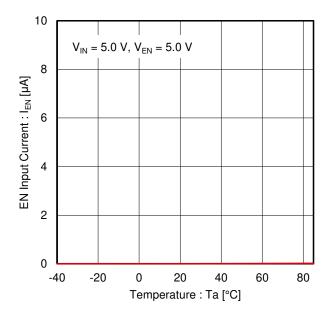
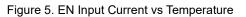


Figure 4. EN Threshold Voltage vs Temperature





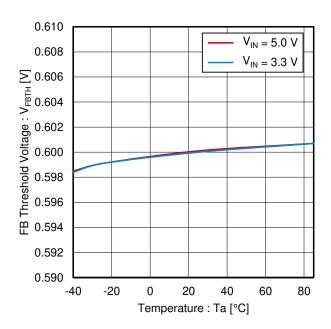


Figure 6. FB Threshold Voltage vs Temperature

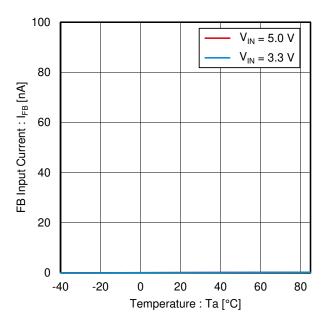


Figure 7. FB Input Current vs Temperature

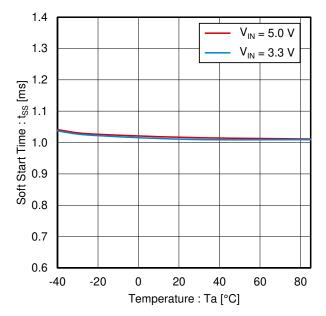


Figure 8. Soft Start Time vs Temperature (SS pin is left floating.)

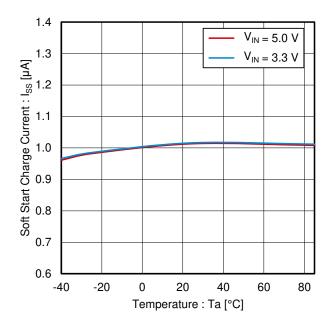


Figure 9. Soft Start Charge Current vs Temperature

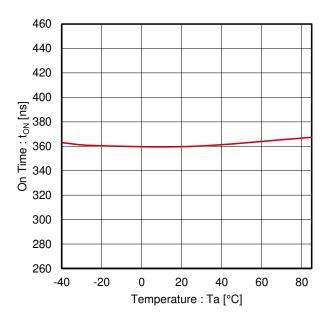


Figure 10. On Time vs Temperature $(V_{IN} = 5.0 \text{ V}, V_{OUT} = 1.8 \text{ V}, I_{OUT} = 1.0 \text{ A})$

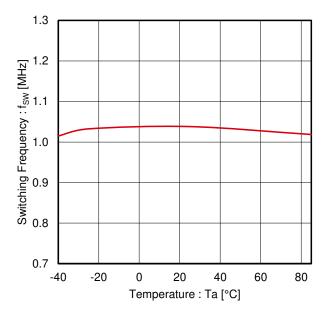


Figure 11. Switching Frequency vs Temperature ($V_{IN} = 5.0 \text{ V}$, $V_{OUT} = 1.8 \text{ V}$, $I_{OUT} = 1.0 \text{ A}$)

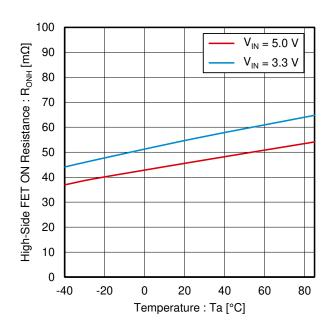
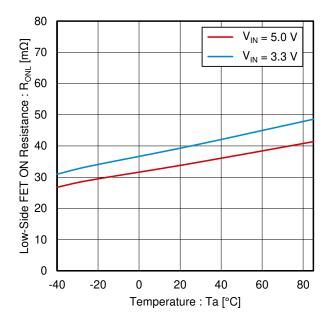


Figure 12. High-Side FET ON Resistance vs Temperature



120
V_{IN} = 5.0 V
Power Fault (V_{FB} rising)

Power Good (V_{FB} falling)

Power Good (V_{FB} falling)

Power Good (V_{FB} falling)

Power Fault (V_{FB} falling)

Power Fault (V_{FB} falling)

Power Fault (V_{FB} falling)

Power Fault (V_{FB} falling)

Temperature : Ta [°C]

Figure 13. Low-Side FET ON Resistance vs Temperature

Figure 14. Power Good / Fault Threshold Voltage vs Temperature

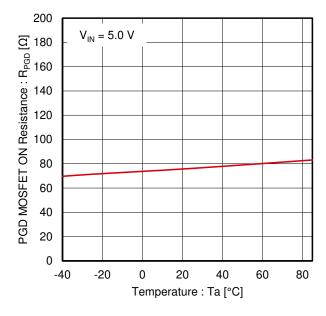


Figure 15. PGD MOSFET ON Resistance vs Temperature

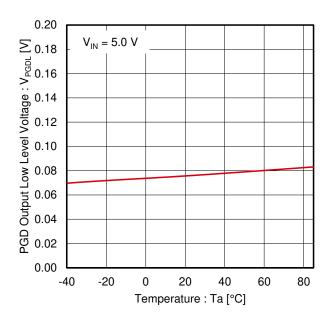
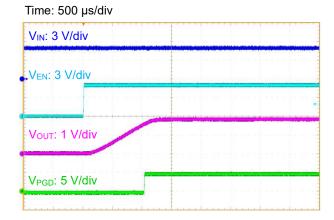


Figure 16. PGD Output Low Level Voltage vs Temperature



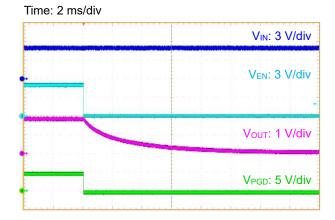
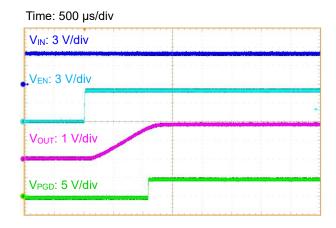


Figure 17. Start-up at No Load: V_{EN} = 0 V to 5 V (V_{IN} = 5.0 V, V_{OUT} = 1.8 V, C_{SS} = OPEN)

Figure 18. Shutdown at No Load: V_{EN} = 5 V to 0 V (V_{IN} = 5.0 V, V_{OUT} = 1.8 V, C_{SS} = OPEN)



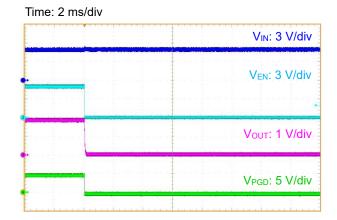


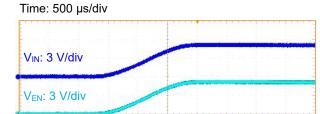
Figure 19. Start-up at R_{Load} = 0.6 Ω : V_{EN} = 0 V to 5 V (V_{IN} = 5.0 V, V_{OUT} = 1.8 V, C_{SS} = OPEN)

Figure 20. Shutdown at R_{Load} = 0.6 Ω : V_{EN} = 5 V to 0 V (V_{IN} = 5.0 V, V_{OUT} = 1.8 V, C_{SS} = OPEN)

V_{OUT}: 1 V/div

V_{PGD}: 5 V/div

Typical Performance Curves - continued

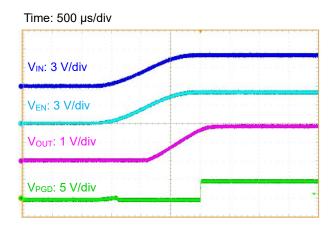


V_{IN}: 3 V/div
V_{EN}: 3 V/div
V_{OUT}: 1 V/div
V_{PGD}: 5 V/div

Time: 2 ms/div

Figure 21. Start-up at No Load: V_{IN} = V_{EN} = 0 V to 5 V (V_{OUT} = 1.8 V, C_{SS} = OPEN)

Figure 22. Shutdown at No Load: $V_{IN} = V_{EN} = 5 \text{ V to } 0 \text{ V}$ ($V_{OUT} = 1.8 \text{ V}, C_{SS} = OPEN$)



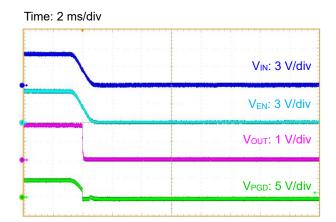
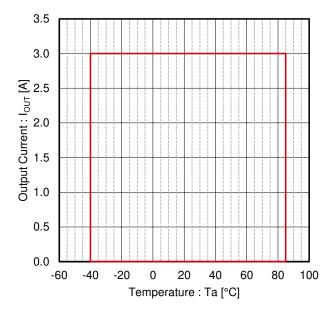


Figure 23. Start-up at R_{Load} = 0.6 Ω : V_{IN} = V_{EN} = 0 V to 5 V (V_{OUT} = 1.8 V, C_{SS} = OPEN)

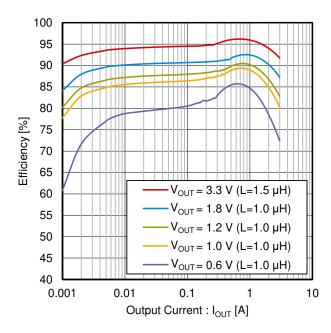
Figure 24. Shutdown at R_{Load} = 0.6 Ω : V_{IN} = V_{EN} = 5 V to 0 V (V_{OUT} = 1.8 V, C_{SS} = OPEN)



3.5 3.0 ₹ 2.5 Output Current : IouT 2.0 1.5 1.0 0.5 0.0 -60 -40 -20 0 20 40 60 80 100 Temperature: Ta [°C]

Figure 25. Output Current vs Temperature $^{(Note\ 1)}$ Operating Range: Tj < 150 °C (V_{IN} = 5.0 V, V_{OUT} = 1.8 V)

Figure 26. Output Current vs Temperature $^{(Note\ 1)}$ Operating Range: Tj < 150 °C (V_{IN} = 3.3 V, V_{OUT} = 1.8 V)



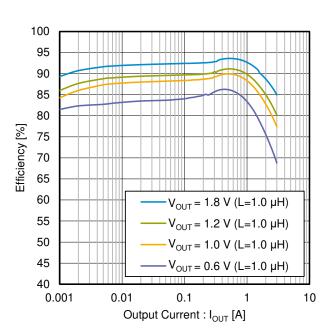
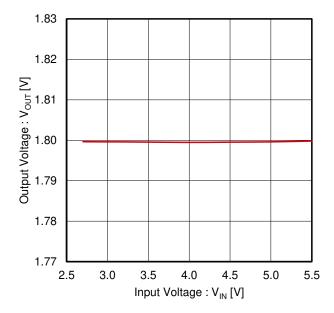


Figure 27. Efficiency vs Output Current (V_{IN} = 5.0 V, L: FDSD0518 series; Murata)

Figure 28. Efficiency vs Output Current ($V_{IN} = 3.3 \text{ V}$, L: FDSD0518 series; Murata)

(Note 1) Measured on FR-4 board 67.5 mm x 67.5 mm, Copper Thickness: Top and Bottom 70 μ m, 2 Internal Layers 35 μ m.



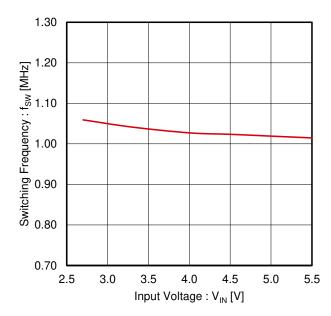


Figure 29. Output Voltage vs Input Voltage (Line Regulation) (V_{OUT} = 1.8 V, I_{OUT} = 1.0 A)

Figure 30. Switching Frequency vs Input Voltage ($V_{OUT} = 1.8 \text{ V}, I_{OUT} = 1.0 \text{ A}$)

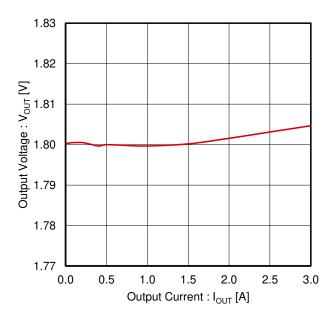


Figure 31. Output Voltage vs Output Current (Load Regulation) ($V_{IN} = 5.0 \text{ V}, V_{OUT} = 1.8 \text{ V}$)

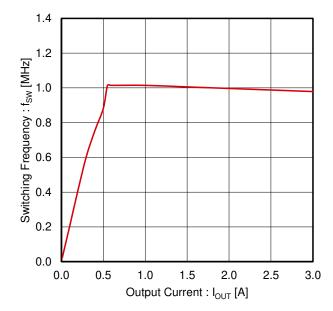
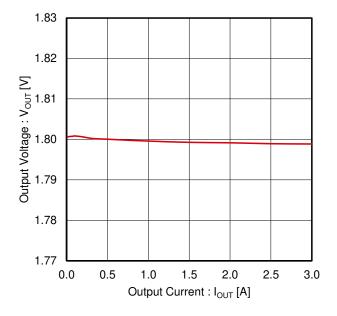


Figure 32. Switching Frequency vs Output Current $(V_{IN} = 5.0 \text{ V}, V_{OUT} = 1.8 \text{ V})$



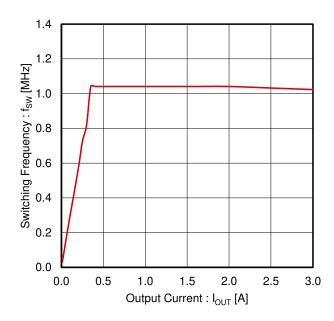
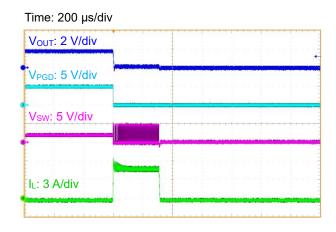


Figure 33. Output Voltage vs Output Current (Load Regulation) ($V_{IN} = 3.3 \text{ V}, V_{OUT} = 1.8 \text{ V}$)

Figure 34. Switching Frequency vs Output Current ($V_{\text{IN}} = 3.3 \text{ V}, V_{\text{OUT}} = 1.8 \text{ V}$)



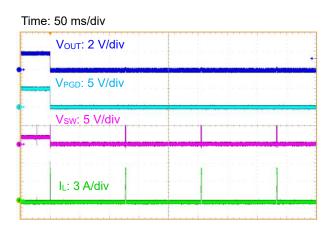


Figure 35. OCP Operation ($V_{IN} = 5.0 \text{ V}$, $V_{OUT} = 1.8 \text{ V}$ to 0 V)

Figure 36. SCP Operation ($V_{IN} = 5.0 \text{ V}$, $V_{OUT} = 1.8 \text{ V}$ to 0 V)

Function Explanations

1. Basic Operation

(1) DC/DC Converter Operation

BD9B305QUZ is a synchronous buck DC/DC converter that achieves faster load transient response due to constant on-time control. The device performs switching operation in PWM (Pulse Width Modulation) control at heavy load. It operates in Light Load Mode control at lighter load to improve efficiency.

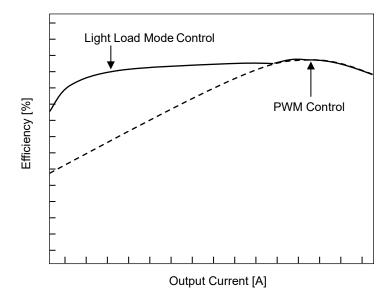


Figure 37. Efficiency Image between Light Load Mode Control and PWM Control

(2) Enable Control

The startup and shutdown can be controlled by the EN voltage (V_{EN}). When V_{EN} becomes 0.920 V (Typ) or more, the internal circuit is activated and the device starts up. When V_{EN} becomes 0.875 V (Typ) or less, the device is shut down. In this shutdown mode, the High-Side FET and the Low-Side FET are turned off and the SW pin is connected to GND through an internal resistor 100 Ω (Typ) to discharge the output. The start-up with V_{EN} must be at the same time of the input voltage V_{IN} ($V_{IN} = V_{EN}$) or after supplying V_{IN} .

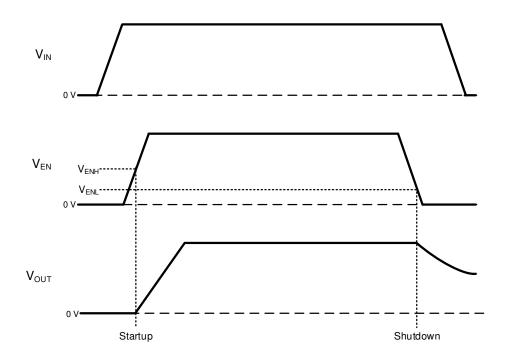


Figure 38. Startup and Shutdown with Enable Control Timing Chart

(3) Soft Start

When V_{EN} goes high, soft start function operates and output voltage gradually rises. This soft start function can prevent overshoot of the output voltage and excessive inrush current. The soft start time t_{SS} is 1 ms (Typ) when the SS pin is left floating. A capacitor connected to the SS pin makes t_{SS} more than 1 ms. See <u>page 31</u> for how to set the soft start time.

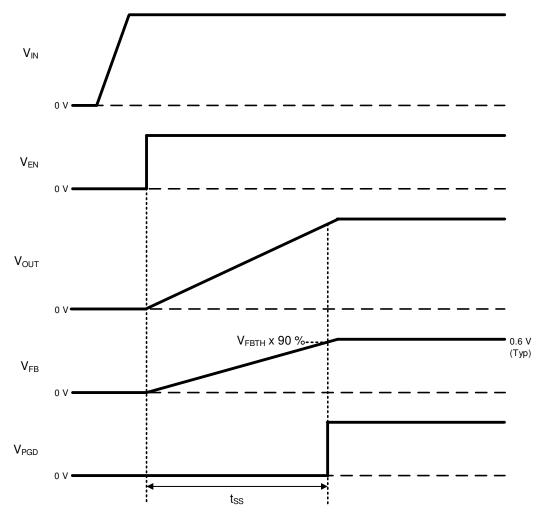


Figure 39. Soft Start Timing Chart

(4) Power Good Output

When the output voltage V_{OUT} reaches within ± 10 % (Typ) of the voltage setting, the built-in open drain Nch MOSFET connected to the PGD pin is turned off, and the PGD pin goes Hi-Z (High impedance). When V_{OUT} reaches outside ± 15 % (Typ) of the voltage setting, the open drain Nch MOSFET is turned on and PGD pin is pulled down with 100 Ω (Typ). It is recommended to connect a pull-up resistor of 10 k Ω to 100 k Ω .

Table 1. PGD Output

State	Condition	PGD Output
Before Supply Input Voltage	V _{IN} < 0.7 V (Typ)	Hi-Z
Shutdown	V _{EN} ≤ 0.875 V (Typ)	Low (Pull-down)
Enable	$90 \% (Typ) \le V_{FB} / V_{FBTH} \le 110 \% (Typ)$	Hi-Z
V _{EN} ≥ 0.920 V (Typ)	V_{FB} / $V_{FBTH} \le 85$ % (Typ) or 115 % (Typ) $\le V_{FB}$ / V_{FBTH}	Low (Pull-down)
UVLO	0.7 V (Typ) < V _{IN} ≤ 2.45 V (Typ)	Low (Pull-down)
TSD	Tj ≥ 175 °C (Typ)	Low (Pull-down)
SCP	Complete Soft Start V _{FB} / V _{FBTH} ≤ 85 % (Typ) OCP 256 counts	Low (Pull-down)

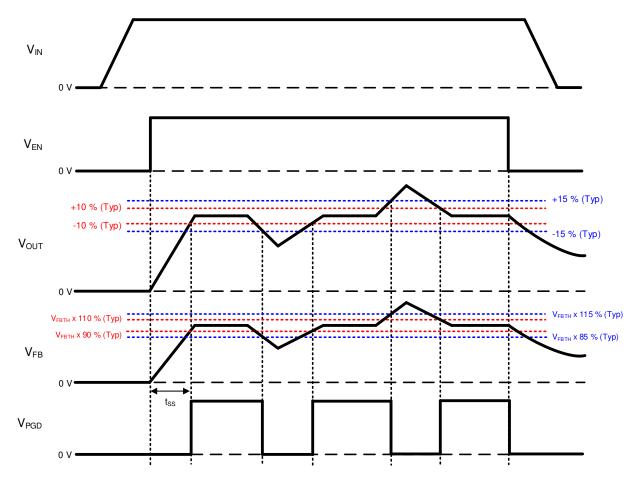


Figure 40. Power Good Timing Chart (Connecting a pull-up resistor to the PGD pin)

(5) Output Capacitor Discharge Function

When even one of the following conditions is satisfied, output is discharged with 100 Ω (Typ) resistor through the SW pin.

- Shutdown: $V_{EN} \le 0.875 \text{ V (Typ)}$
- UVLO: $V_{IN} \le 2.45 \text{ V (Typ)}$
- TSD: Tj ≥ 175 °C (Typ)
- SCP: Complete Soft Start, V_{FB} / V_{FBTH} ≤ 85 % (Typ), and OCP 256 counts

When all of the above conditions are released, output discharge is stopped.

2. Protection

The protection circuits are intended for prevention of damage caused by unexpected accidents. Do not use the continuous protection.

(1) Over Current Protection (OCP) / Short Circuit Protection (SCP)

Over Current Protection (OCP) restricts the flowing current through the Low-Side FET and the High-Side FET for every switching period. If the inductor current exceeds the Low-Side OCP $I_{LOCP} = 4.5$ A (Typ) while the Low-Side FET is on, the Low-Side FET remains on even with FB voltage V_{FB} falls to $V_{FBTH} = 0.6$ V (Typ) or lower. If the inductor current becomes lower than I_{LOCP} , the High-Side FET is able to be turned on. When the inductor current becomes the High-Side OCP $I_{HOCP} = 6.5$ A (Typ) or more while the High-Side FET is on, the High-Side FET is turned off. Output voltage may decrease by changing frequency and duty due to the OCP operation.

Short Circuit Protection (SCP) function is a Hiccup mode. When Low-Side OCP operates 256 cycles while V_{FB} is V_{FBTH} x 85 % or less (V_{PGD} = Low), the device stops the switching operation for 128 ms (Typ). After the 128 ms (Typ), the device restarts. SCP does not operate during the soft start even if the device is in the SCP conditions. Do not exceed the maximum junction temperature (Tjmax = 150 °C) during OCP and SCP operation.

Table 2. The Operating Condition of OCP and SCP

V _{EN}	V _{FB}	Start-up	OCP	SCP
	≤ V _{FBTH} x 85 % (Typ)	During Soft Start	Enable	Disable
≥ 0.920 V (Typ)	> V _{FВТН} х 85 % (Тур)	Complete Soft Start	Enable	Disable
	≤ V _{FBTH} x 85 % (Typ)	Complete Soft Start	Enable	Enable
≤ 0.875 V (Typ)	-	Shutdown	Disable	Disable

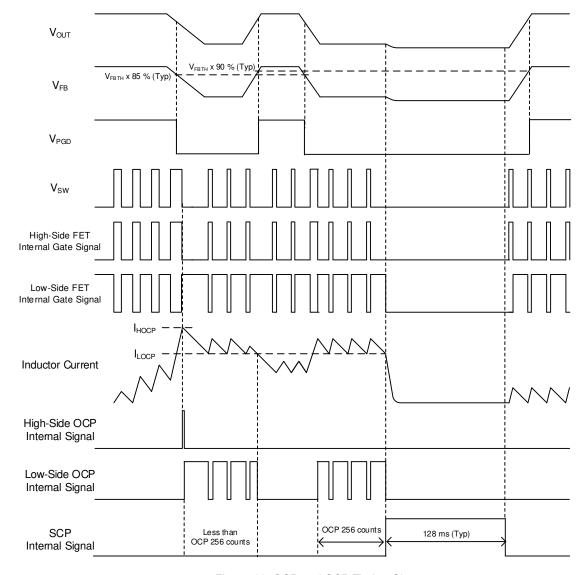


Figure 41. OCP and SCP Timing Chart

(2) Under Voltage Lockout Protection (UVLO)

When input voltage V_{IN} falls to 2.45 V (Typ) or lower, the device is shut down. When V_{IN} becomes 2.55 V (Typ) or more, the device starts up. The hysteresis is 100 mV (Typ).

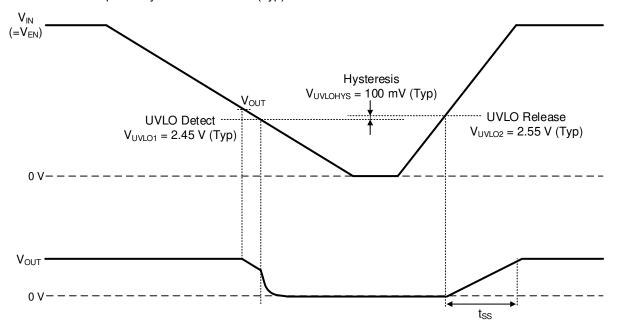


Figure 42. UVLO Timing Chart

(3) Thermal Shutdown Protection (TSD)

Thermal shutdown circuit prevents heat damage to the IC. The device should always operate within the IC's maximum junction temperature rating (Tjmax = $150~^{\circ}$ C). However, if it continues exceeding the rating and the junction temperature Tj rises to $175~^{\circ}$ C (Typ), the TSD circuit is activated and it turns the output MOSFETs off. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation. The TSD threshold has a hysteresis of $25~^{\circ}$ C (Typ). Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings. Therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

(4) Over Voltage Protection (OVP)

When the FB voltage V_{FB} exceeds V_{FBTH} x 115 % (Typ) or more, the output MOSFETs are turned off to prevent the increase in the output voltage. After the V_{FB} falls V_{FBTH} x 110 % (Typ) or less, the output MOSFETs are returned to normal operation condition. Switching operation will restart after V_{FB} falls below V_{FBTH} .

Application Examples

1. V_{IN} = 5 V, V_{OUT} = 3.3 V

Table 3. Specification of Application (V_{IN} = 5 V, V_{OUT} = 3.3 V)

Parameter	Symbol	Specification Value
Input Voltage	Vin	5 V (Typ)
Output Voltage	Vout	3.3 V (Typ)
Maximum Output Current	loutmax	3.0 A
Switching Frequency	f _{SW}	1.0 MHz (Typ)
Soft Start Time	tss	1 ms (Typ)
Temperature	Та	25 °C

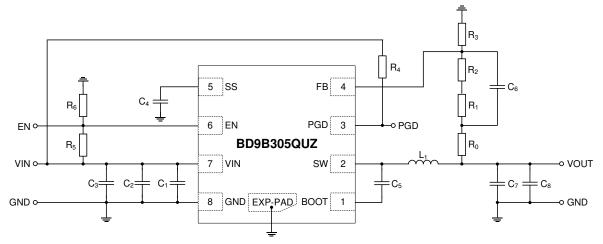


Figure 43. Application Circuit

Table 4. Recommended Component Values (V_{IN} = 5 V, V_{OUT} = 3.3 V)

Part No.	Value	Part Name	Size Code (mm)	Manufacturer
L ₁	1.5 µH	FDSD0518-H-1R5M	5249	Murata
C ₁ (Note 1)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₂ (Note 2)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
C ₃ (Note 2)	-	-	-	-
C ₄	-	-	-	-
C ₅ (Note 3)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₆	100 pF (50 V, C0G, ±5 %)	GRM0335C1H101JA01	0603	Murata
C ₇ (Note 4)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
C ₈ (Note 4)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
R ₁	200 kΩ (1 %, 1/16 W)	MCR01MZPF2003	1005	ROHM
R ₂	12 kΩ (1 %, 1/16 W)	MCR01MZPF1202	1005	ROHM
R ₃	47 kΩ (1 %, 1/16 W)	MCR01MZPF4702	1005	ROHM
R ₄	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₅	1.8 MΩ (1 %, 1/16 W)	MCR01MZPF1804	1005	ROHM
R ₆	470 kΩ (1 %, 1/16 W)	MCR01MZPF4703	1005	ROHM
R ₀ (Note 5)	Short	-	-	-

⁽Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor C₁ as close as possible to the VIN pin and the GND

pin if needed. (Note 2) For the input capacitor C_2 and C_3 , take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 4.7 μF.

⁽Note 3) For the bootstrap capacitor C5, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

⁽Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C_7 and C8, the loop response characteristics may change. Confirm with the actual application. The total capacitance of 10 µF to 47 x 2 µF is recommended for the output capacitor.

⁽Note 5) R₀ is an option, used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit

1. V_{IN} = 5 V, V_{OUT} = 3.3 V – continued

Time: 2 μs/div

Vout: 20 mV/div

Vsw: 2 V/div

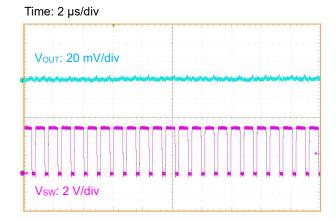
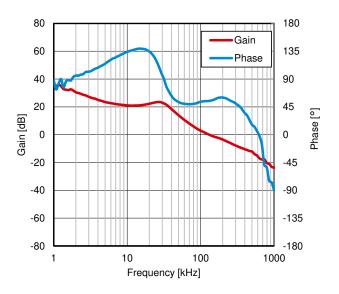


Figure 44. Output Ripple Voltage (I_{OUT} = 0.1 A)

Figure 45. Output Ripple Voltage (I_{OUT} = 3.0 A)



Time: 100 μs/div

Vour: 200 mV/div

Iouτ: 500 mA/div

Figure 46. Frequency Characteristics (I_{OUT} = 3.0 A)

Figure 47. Load Transient Response (I_{OUT} = 0.1 A to 1.0 A)

Application Examples - continued

2. $V_{IN} = 5 V$, $V_{OUT} = 1.8 V$

Table 5. Specification of Application (V_{IN} = 5 V, V_{OUT} = 1.8 V)

Parameter	Symbol	Specification Value
Input Voltage	Vin	5 V (Typ)
Output Voltage	Vouт	1.8 V (Typ)
Maximum Output Current	Іоитмах	3.0 A
Switching Frequency	f _{SW}	1.0 MHz (Typ)
Soft Start Time	tss	1 ms (Typ)
Temperature	Та	25 °C

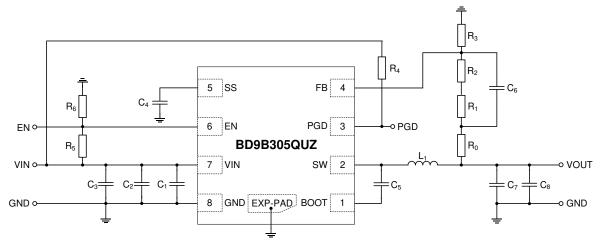


Figure 48. Application Circuit

Table 6. Recommended Component Values (VIN = 5 V, VOUT = 1.8 V)

Part No.	Value	Part Name	Size Code (mm)	Manufacturer
L ₁	1.0 µH	FDSD0518-H-1R0M	5249	Murata
C ₁ (Note 1)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₂ (Note 2)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
C ₃ (Note 2)	-	-	-	-
C ₄	-	-	-	-
C ₅ (Note 3)	0.1 μF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₆	100 pF (50 V, C0G, ±5 %)	GRM0335C1H101JA01	0603	Murata
C ₇ (Note 4)	47 μF (4 V, X5R, ±20 %)	AMK107BBJ476MA-RE	1608	TAIYO YUDEN
C ₈ (Note 4)	-	-	-	-
R ₁	200 kΩ (1 %, 1/16 W)	MCR01MZPF2003	1005	ROHM
R ₂	Short	-	-	-
R ₃	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₄	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₅	-	-	-	-
R ₆	-	-	-	-
R ₀ (Note 5)	Short		-	-

⁽Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor C₁ as close as possible to the VIN pin and the GND

pin if needed.
(Note 2) For the input capacitor C_2 and C_3 , take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 4.7 μF.

⁽Note 3) For the bootstrap capacitor C5, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

⁽Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C₇ and C8, the loop response characteristics may change. Confirm with the actual application. The total capacitance of 10 µF to 47 x 2 µF is recommended for the output capacitor.

⁽Note 5) R₀ is an option, used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit

2. V_{IN} = 5 V, V_{OUT} = 1.8 V - continued



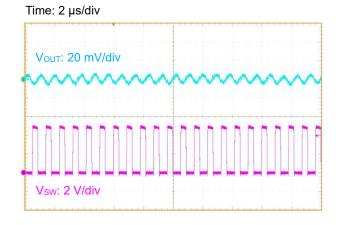
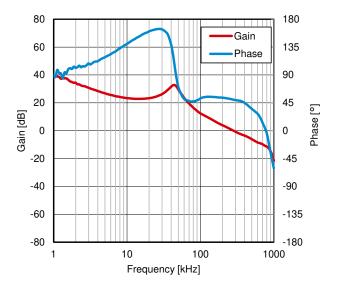


Figure 49. Output Ripple Voltage (Iout = 0.1 A)

Figure 50. Output Ripple Voltage (Iout = 3.0 A)



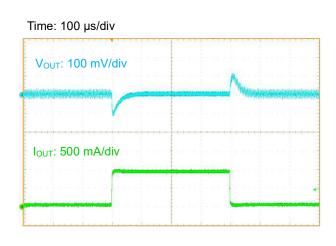


Figure 51. Frequency Characteristics (I_{OUT} = 3.0 A)

Figure 52. Load Transient Response (I_{OUT} = 0.1 A to 1.0 A)

Application Examples - continued

3. $V_{IN} = 5 V$, $V_{OUT} = 1.2 V$

Table 7. Specification of Application (V_{IN} = 5 V, V_{OUT} = 1.2 V)

Symbol	Specification Value		
Vin	5 V (Typ)		
Vouт	1.2 V (Typ)		
Гоитмах	3.0 A		
fsw	1.0 MHz (Typ)		
tss	1 ms (Typ)		
Та	25 °C		
	Symbol VIN VOUT IOUTMAX fsw tss		

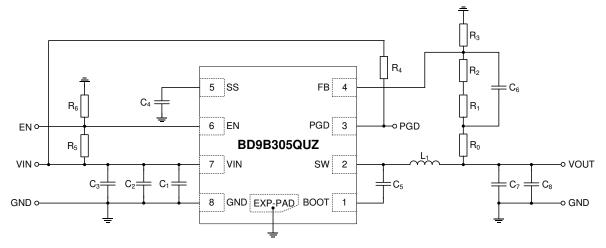


Figure 53. Application Circuit

Table 8. Recommended Component Values (VIN = 5 V, VOUT = 1.2 V)

Part No.	Value Part Name		Size Code (mm)	Manufacturer
L ₁	1.0 µH	FDSD0518-H-1R0M	D0518-H-1R0M 5249	
C ₁ (Note 1)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₂ (Note 2)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
C ₃ (Note 2)	-	-	-	-
C ₄	-	-	-	-
C ₅ (Note 3)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₆	120 pF (50 V, C0G, ±5 %)	GRM0335C1H121JA01	0603	Murata
C ₇ (Note 4)	47 μF (4 V, X5R, ±20 %)	AMK107BBJ476MA-RE	1608	TAIYO YUDEN
C ₈ (Note 4)	-	-	-	-
R ₁	150 kΩ (1 %, 1/16 W)	MCR01MZPF1503	1005	ROHM
R ₂	Short	-	-	-
R ₃	150 kΩ (1 %, 1/16 W)	MCR01MZPF1503	1005	ROHM
R ₄	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₅	-	-	-	-
R ₆	-	-	-	-
R ₀ (Note 5)	Short	-	-	-

⁽Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor C1 as close as possible to the VIN pin and the GND

pin if needed. (Note 2) For the input capacitor C_2 and C_3 , take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 4.7 μF.

⁽Note 3) For the bootstrap capacitor C5, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

⁽Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C₇ and C8, the loop response characteristics may change. Confirm with the actual application. The total capacitance of 10 µF to 47 x 2 µF is recommended for the output capacitor.

⁽Note 5) R₀ is an option, used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit

3. V_{IN} = 5 V, V_{OUT} = 1.2 V - continued

Time: 2 μs/div

Vout: 20 mV/div

Vsw: 2 V/div

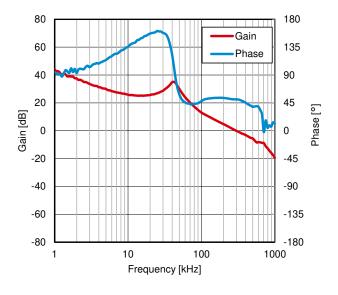
Time: 2 μs/div

Vouτ: 20 mV/div

Vsw: 2 V/div

Figure 54. Output Ripple Voltage (Iout = 0.1 A)

Figure 55. Output Ripple Voltage (I_{OUT} = 3.0 A)



Time: 100 µs/div

Vout: 100 mV/div

Iout: 500 mA/div

Figure 56. Frequency Characteristics (I_{OUT} = 3.0 A)

Figure 57. Load Transient Response (I_{OUT} = 0.1 A to 1.0 A)

Application Examples - continued

4. $V_{IN} = 5 V$, $V_{OUT} = 1.0 V$

Table 9. Specification of Application (V_{IN} = 5 V, V_{OUT} = 1.0 V)

Parameter	Symbol	Specification Value
Input Voltage	V _{IN}	5 V (Typ)
Output Voltage	Vout	1.0 V (Typ)
Maximum Output Current	loutmax	3.0 A
Switching Frequency	f _{SW}	1.0 MHz (Typ)
Soft Start Time	tss	1 ms (Typ)
Temperature	Та	25 °C

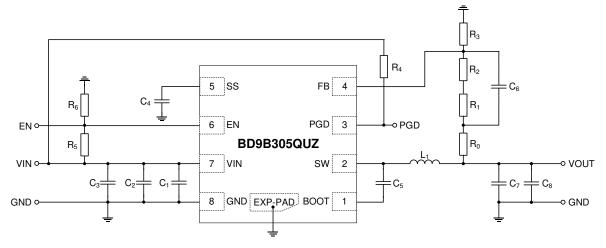


Figure 58. Application Circuit

Table 10. Recommended Component Values (V_{IN} = 5 V, V_{OUT} = 1.0 V)

Part No.	Value	Part Name	Size Code (mm)	Manufacturer
L ₁	1.0 µH	FDSD0518-H-1R0M	5249	Murata
C ₁ (Note 1)	0.1 μF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₂ (Note 2)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
C ₃ (Note 2)	-	-	-	-
C ₄	-	-	-	-
C ₅ (Note 3)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₆	120 pF (50 V, C0G, ±5 %)	GRM0335C1H121JA01	0603	Murata
C ₇ (Note 4)	47 μF (4 V, X5R, ±20 %)	AMK107BBJ476MA-RE	1608	TAIYO YUDEN
C ₈ (Note 4)	-	-	-	•
R ₁	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₂	Short	-	-	-
R ₃	150 kΩ (1 %, 1/16 W)	MCR01MZPF1503	1005	ROHM
R ₄	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₅	-	-	-	-
R ₆			-	-
R ₀ (Note 5)	Short	-	-	-

⁽Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor C₁ as close as possible to the VIN pin and the GND

pin if needed. (Note 2) For the input capacitor C_2 and C_3 , take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 4.7 μF.

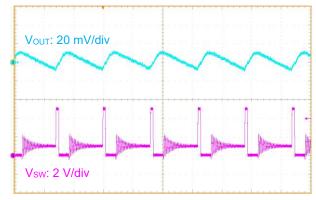
⁽Note 3) For the bootstrap capacitor C5, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 μF .

⁽Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C_7 and C8, the loop response characteristics may change. Confirm with the actual application. The total capacitance of 10 µF to 47 x 2 µF is recommended for the output capacitor.

⁽Note 5) R₀ is an option, used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit

4. V_{IN} = 5 V, V_{OUT} = 1.0 V - continued

Time: 2 µs/div



Time: 2 µs/div

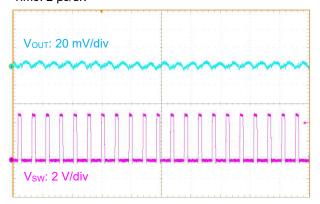
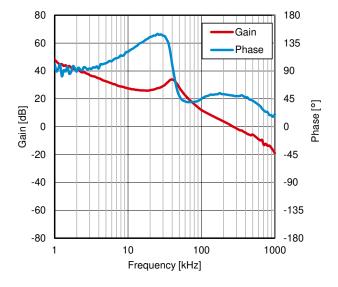


Figure 59. Output Ripple Voltage (Iout = 0.1 A)

Figure 60. Output Ripple Voltage (Iout = 3.0 A)



Time: 100 μs/div

Vouτ: 100 mV/div

Iouτ: 500 mA/div

Figure 61. Frequency Characteristics (I_{OUT} = 3.0 A)

Figure 62. Load Transient Response (I_{OUT} = 0.1 A to 1.0 A)

Application Examples - continued

5. V_{IN} = 5 V, V_{OUT} = 0.6 V

Table 11. Specification of Application (V_{IN} = 5 V, V_{OUT} = 0.6 V)

Specification Value
5 \/ (Tvp)
5 V (Typ)
0.6 V (Typ)
3.0 A
1.0 MHz (Typ)
1 ms (Typ)
25 °C

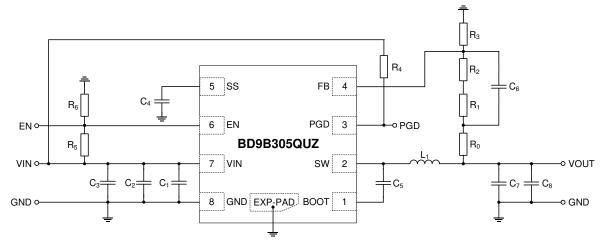


Figure 63. Application Circuit

Table 12. Recommended Component Values (V_{IN} = 5 V, V_{OUT} = 0.6 V)

Part No.	Value Part Name Size		Size Code (mm)	Manufacturer
L ₁	1.0 µH	FDSD0518-H-1R0M 5249		Murata
C ₁ (Note 1)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₂ (Note 2)	22 μF (10V, X5R, ±20 %)	GRM188R61A226ME15	1608	Murata
C ₃ (Note 2)	-	-	-	-
C ₄	-	-	-	-
C ₅ (Note 3)	0.1 µF (16V, X5R, ±10 %)	GRM033R61C104KE14	0603	Murata
C ₆	120 pF (50 V, C0G, ±5 %)	GRM0335C1H121JA01	0603	Murata
C ₇ (Note 4)	47 μF (4 V, X5R, ±20 %)	AMK107BBJ476MA-RE	1608	TAIYO YUDEN
C ₈ (Note 4)	-	-	-	-
R ₁	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₂	Short	-	-	-
R ₃	-	-	-	-
R ₄	100 kΩ (1 %, 1/16 W)	MCR01MZPF1003	1005	ROHM
R ₅	-	-	-	-
R ₆	-	-	-	-
R ₀ (Note 5)	Short	-	-	-

⁽Note 1) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor C1 as close as possible to the VIN pin and the GND

pin if needed. (Note 2) For the input capacitor C_2 and C_3 , take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 4.7 μF.

⁽Note 3) For the bootstrap capacitor C5, take temperature characteristics, DC bias characteristics, etc. into consideration to set to the actual capacitance of no less than 0.022 µF.

⁽Note 4) In case of changing the actual capacitance value due to temperature characteristics, DC bias characteristics, etc. of the output capacitor C7 and C8, the loop response characteristics may change. Confirm with the actual application. The total capacitance of 10 µF to 47 x 2 µF is recommended for the output capacitor.

⁽Note 5) R₀ is an option, used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit

Vsw: 2 V/div

5. V_{IN} = 5 V, V_{OUT} = 0.6 V – continued

Time: 2 μs/div

Vouτ: 20 mV/div

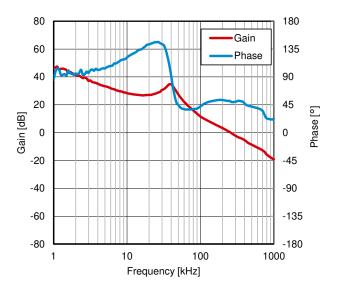
Time: 2 μs/div

Vouτ: 20 mV/div

Vsw: 2 V/div

Figure 64. Output Ripple Voltage (I_{OUT} = 0.1 A)

Figure 65. Output Ripple Voltage (Iout = 3.0 A)



Time: 100 µs/div

Vout: 100 mV/div

Iout: 500 mA/div

Figure 66. Frequency Characteristics (I_{OUT} = 3.0 A)

Figure 67. Load Transient Response (I_{OUT} = 0.1 A to 1.0 A)

Selection of Components Externally Connected

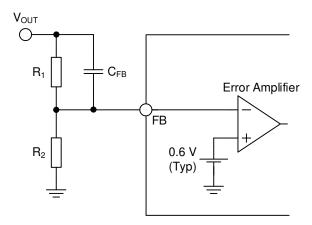
Contact us if not use the recommended component values in Application Examples.

1. Input Capacitor

Use ceramic type capacitor for the input capacitor. The input capacitor is used to reduce the input ripple noise and it is effective by being placed as close as possible to the VIN pin. Set the capacitor value so that it does not fall to 4.7 μ F considering the capacitor value variances, temperature characteristics, DC bias characteristics, aging characteristics, and etc. The PCB layout and the position of the capacitor may lead to IC malfunction. Refer to the notes on the PCB layout on page 34 to 35 when designing PCB layout. In addition, the capacitor with value 0.1 μ F can be connected as close as possible to the VIN pin and the GND pin in order to reduce the high frequency noise.

2. Output Voltage Setting

The output voltage can be set by the feedback resistance ratio connected to the FB pin. For stable operation, the parallel resistance of feedback resistors R_1 and R_2 should be set to 20 k Ω or more.



The output voltage Vout can be calculated as below.

$$V_{OUT} = \frac{R_1 + R_2}{R_2} \times 0.6$$
 [V]

$$0.6 \le V_{OUT} \le (V_{IN} \times 0.8)$$
 [V]

$$1/(\frac{1}{R_1} + \frac{1}{R_2}) \ge 20 \text{ [k}\Omega]$$

Figure 68. Feedback Resistor Circuit

3. Soft Start Capacitor (Soft Start Time Setting)

The soft start time t_{SS} depends on the value of the capacitor connected to the SS pin. The t_{SS} is 1 ms (Typ) when the SS pin is left floating. The capacitor connected to the SS pin makes t_{SS} more than 1 ms. The t_{SS} and t_{SS} can be calculated using below equation. The t_{SS} should be set in the range between 3300 pF and 0.1 t_{SS}

$$t_{SS} = \frac{C_{SS} \times 0.6}{I_{SS}}$$
 [s]

where:

 I_{SS} is the Soft Start Charge Current 1.0 μ A (Typ).

With Css = 8200 pF, tss can be calculated as below.

$$t_{SS} = \frac{8200 \ pF \times 0.6}{1.0 \ \mu A} = 4.9 \ [\text{ms}]$$

Selection of Components Externally Connected - continued

4. Output LC Filter

In order to supply a continuous current to the load, the DC/DC converter requires an LC filter for smoothing the output voltage. Use the inductor with value 1.0 μ H to 1.5 μ H.

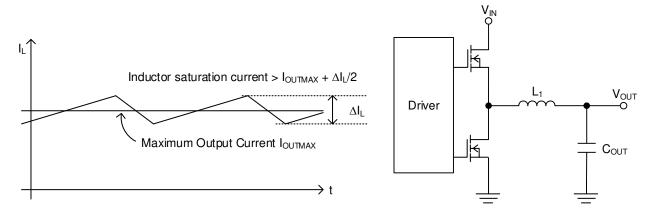


Figure 69. Waveform of Inductor Current

Figure 70. Output LC Filter Circuit

For example, given that V_{IN} = 5 V, V_{OUT} = 1.8 V, L_1 = 1.0 μ H, and the switching frequency f_{SW} = 1.0 MHz, Inductor current ΔI_L can be represented by the following equation.

$$\Delta I_L = V_{OUT} \times (V_{IN} - V_{OUT}) \times \frac{1}{V_{IN} \times f_{SW} \times L_1} = 1.15$$
 [A]

The rated current of the inductor (Inductor saturation current) must be larger than the sum of the maximum output current I_{OUTMAX} and 1/2 of the inductor ripple current ΔI_L .

Use ceramic type capacitor for the output capacitor C_{OUT} . The capacitance value of C_{OUT} is recommended in the range between 10 μ F and 47 x 2 μ F. C_{OUT} affects the output ripple voltage. Select C_{OUT} so that it must satisfy the required ripple voltage characteristics.

The output ripple voltage can be estimated by the following equation.

$$\Delta V_{RPL} = \Delta I_L \times \left(R_{ESR} + \frac{1}{8 \times C_{OUT} \times f_{SW}} \right)$$
 [V]

where:

 R_{ESR} is the Equivalent Series Resistance (ESR) of the output capacitor.

For example, given that C_{OUT} = 47 μF and R_{ESR} = 3 $m\Omega$, ΔV_{RPL} can be calculated as below.

$$\Delta V_{RPL} = 1.15 A \times \left(3 m\Omega + \frac{1}{8 \times 47 \mu F \times 1 MHz}\right) = 6.5 \text{ [mV]}$$

4. Output LC Filter - continued

In addition, the total capacitance connected to V_{OUT} needs to satisfy the value obtained by the following equation.

$$C_{OUTMAX} < \frac{t_{SSMIN}}{V_{OUT}} \times (3.1 + \frac{\Delta I_L}{2} - I_{OUTSS})$$
 [F]

where:

 $t_{\it SSMIN}$ is the minimum soft start time.

 V_{OUT} is the output voltage.

 ΔI_L is the inductor current.

 I_{OUTSS} is the maximum output current during soft start.

For example, given that V_{IN} = 5 V, V_{OUT} = 1.8 V, L_1 = 1.0 μ H, f_{SW} = 1 MHz (Typ), t_{SSMIN} = 0.6 ms (C_{SS} = OPEN), and I_{OUTSS} = 3 A, C_{OUTMAX} can be calculated as below.

$$C_{OUTMAX} < \frac{0.6 \text{ ms}}{1.8 \text{ V}} \times (3.1 + \frac{1.15 \text{ A}}{2} - 3 \text{ A}) = 225 \text{ [µF]}$$

If the total capacitance connected to V_{OUT} is larger than C_{OUTMAX}, over current protection may be activated by the inrush current at startup and prevented to turn on the output. Confirm this on the actual application.

5. FB Capacitor

The Constant On-time Control required the sufficient ripple voltage on FB voltage for the operation stability. This device is designed to correspond to low ESR output capacitors by injecting the ripple voltage to FB voltage inside the IC. The FB capacitor CFB (Figure 68) should be set within the range of the following expression in order to inject an appropriate ripple.

$$\frac{v_{out} \times (1 - v_{out}/v_{IN})}{f_{SW} \times 21 \times 10^3} < C_{FB} < \frac{v_{out} \times (1 - v_{out}/v_{IN})}{f_{SW} \times 3.3 \times 10^3} \text{ [F]}$$

where:

 V_{IN} is the input voltage.

 V_{OUT} is the output voltage.

 f_{SW} is the switching frequency 1.0 MHz (Typ).

Load transient response and the loop stability depends on L_1 , C_{OUT} , and C_{FB} . Actually, these characteristics may change depending on PCB layout, wiring, the type of components, and the conditions (temperature, etc.). Be sure to check them on the actual application.

6. Bootstrap Capacitor

The bootstrap capacitor $0.1\mu F$ is recommended. Connect the capacitor between the SW pin and the BOOT pin. For the capacitance, take temperature characteristics, DC bias characteristics, and etc. into consideration to set to the actual capacitance of no less than $0.022 \ \mu F$.

PCB Layout Design

PCB layout design for DC/DC converter is very important. Appropriate layout can avoid various problems concerning power supply circuit. Figure 71-a to Figure 71-c show the current path in a buck DC/DC converter circuit. The Loop 1 in Figure 71-a is a current path when H-side switch is ON and L-side switch is OFF, the Loop 2 in Figure 71-b is when H-side switch is OFF and L-side switch is ON. The thick line in Figure 71-c shows the difference between Loop1 and Loop2. The current in thick line change sharply each time the switching element H-side and L-side switch change from OFF to ON, and vice versa. These sharp changes induce a waveform with harmonics in this loop. Therefore, the loop area of thick line that is consisted by input capacitor and IC should be as small as possible to minimize noise. For more details, refer to application note of switching regulator series "PCB Layout Techniques of Buck Converter".

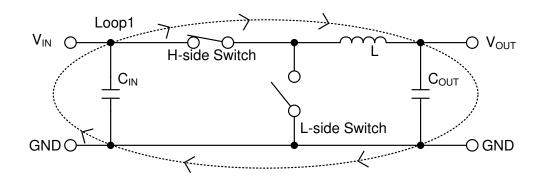


Figure 71-a. Current Path when H-side Switch = ON, L-side Switch = OFF

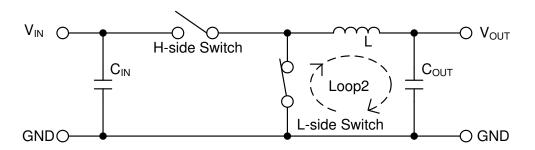


Figure 71-b. Current Path when H-side Switch = OFF, L-side Switch = ON

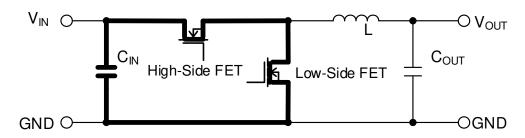


Figure 71-c. Difference of Current and Critical Area in Layout

PCB Layout Design - continued

When designing the PCB layout, pay attention to the following points:

- Connect the input capacitor C_{IN1} and C_{IN2} as close as possible to the VIN pin and GND pin on the same plane as the IC.
- Switching nodes such as SW are susceptible to noise due to AC coupling with other nodes. Route the inductor pattern L₁ as thick and as short as possible.
- Feedback line connected to the FB pin far from the SW nodes.
- Place the output capacitor C_{OUT} away from input capacitor C_{IN1} and C_{IN2} to avoid harmonics noise from the input.
- Separate the reference ground and the power ground and connect them through VIA. The reference ground should be connected to the power ground that is close to the output capacitor Cout. It is because Cout has less high frequency switching noise.
- R₀ is provided for the measurement of feedback frequency characteristics (optional). By inserting a resistor into R₀, it is possible to measure the frequency characteristics of feedback (phase margin) using FRA etc. R₀ is short-circuited for normal use.

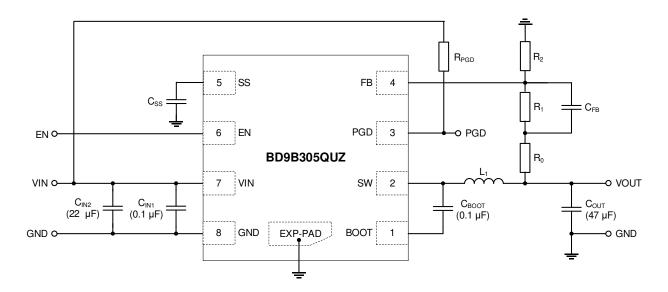


Figure 72. Application Circuit

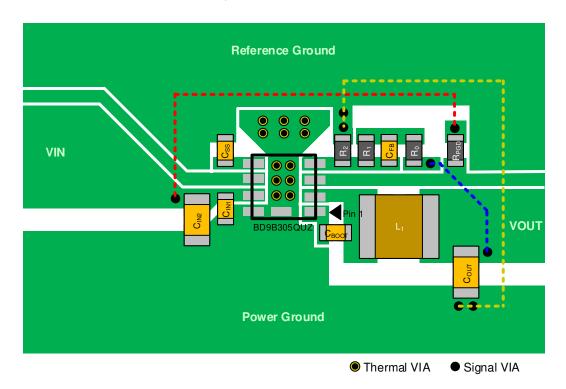
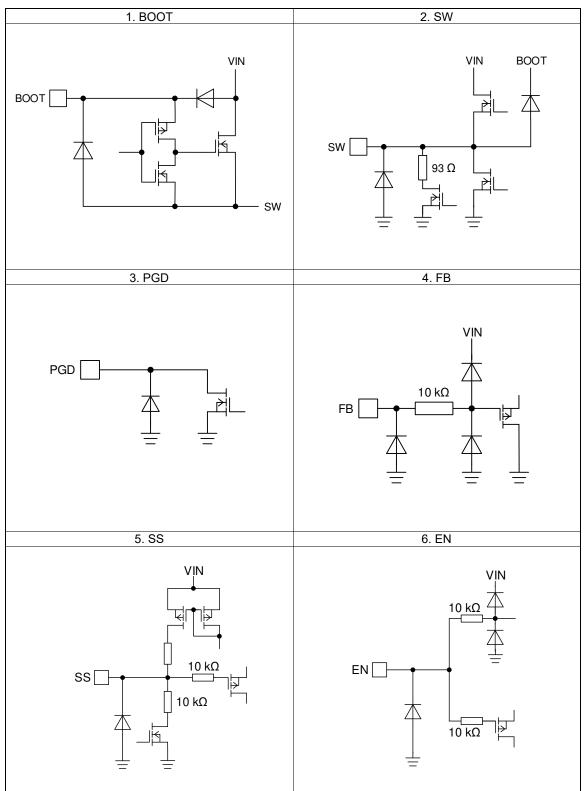


Figure 73. Example of PCB Layout

I/O Equivalence Circuits



Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition. However, pins that drive inductive loads (e.g. motor driver outputs, DC-DC converter outputs) may inevitably go below ground due to back EMF or electromotive force. In such cases, the user should make sure that such voltages going below ground will not cause the IC and the system to malfunction by examining carefully all relevant factors and conditions such as motor characteristics, supply voltage, operating frequency and PCB wiring to name a few.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operational Notes - continued

10. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

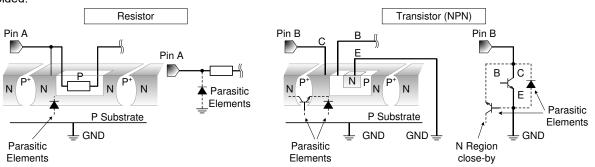


Figure 74. Example of Monolithic IC Structure

11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

12. Thermal Shutdown Circuit (TSD)

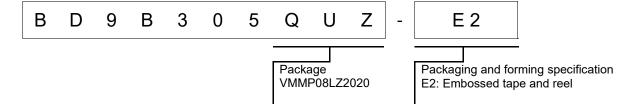
This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF power output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

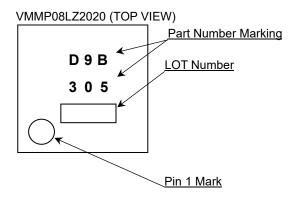
13. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

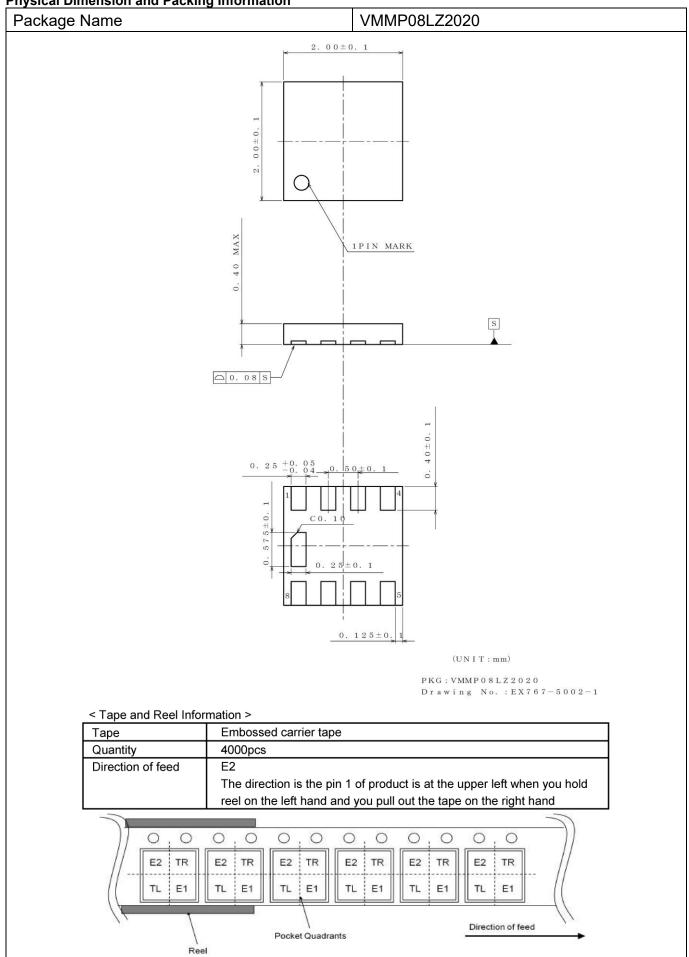
Ordering Information



Marking Diagram



Physical Dimension and Packing Information



Revision History

Date	Revision	Changes	
08.Mar.2019	001	New Release	
20.Feb.2023	002	Change the recommended components C ₆ , C ₇ and C ₈ in Table 4. Update Figure 44, Figure 45, Figure 46 and Figure 47.	

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